(b) Amendments to the Claims

A detailed listing of all the claims that are or were pending is provided which replaces all earlier versions.

1. (Currently Amended) A deposited-film formation process in which a source gas is fed into a discharge space of a reactor, a plurality of discharge means are disposed in the reactor and an electric power is applied to generate discharge in the discharge space to decompose the source gas, thereby forming a deposited film on a beltlike substrate the process comprising transporting the beltlike substrate through the reactor during the film formation and having:

a first step of applying an electric power to a first discharge means to generate discharge to form the deposited film; and

a second step of applying an electric power to a second discharge means to generate discharge to form the deposited film, said first and second discharge means each being electrodes connected to an RF power source;

said first step and said second step being switched from one to another when film formation temperature is above a preset temperature, wherein the deposited film formed through said first step and the deposited film formed through said second step are semiconductor layers having the same conductivity type, and the deposited film formed through said second step is at a position on the beltlike substrate different from a position of the deposited film formed through said first step .

2. (Currently Amended) A deposited-film formation process in which a source gas is fed into a discharge space of a reactor, a plurality of discharge means are disposed in the reactor and an electric power is applied to generate discharge in the discharge space to decompose the source gas, thereby forming a deposited film on a beltlike substrate; the process comprising transporting the beltlike substrate through the reactor during the film formation and having:

a first step of applying to a first discharge means an electric power larger than that for a second discharge means to generate discharge to form the deposited film; and

a second step of applying to the second discharge means an electric power larger than that for the first discharge means to generate discharge to form the deposited film, said first and second discharge means each being electrodes connected to an RF power source;

said first step and said second step being switched from one to another when film formation temperature is above a preset temperature wherein the deposited film formed through said first step and the deposited film formed through said second step are semiconductor layers having the same conductivity type, and the deposited film formed through said second step is at a position on the beltlike substrate different from a position of the deposited film formed through said first step .

3. (Currently Amended) A deposited-film formation process

in which a source gas is fed into a discharge space of a reactor, a plurality of discharge means are disposed in the reactor and an electric power is applied to generate discharge in the discharge space to decompose the source gas, thereby forming a deposited film on a beltlike substrate; the process comprising transporting the beltlike substrate through the reactor during the film formation and having:

a first step of applying an electric power to a first discharge means in a first reactor to generate discharge to form the deposited film; and

a second step of applying an electric power to a second discharge means in a second reactor to generate discharge to form the deposited film, said first and second discharge means each being electrodes connected to an RF power source;

said first step and said second step being switched from one to another when film formation temperature is above a preset temperature wherein the deposited film formed through said first step and the deposited film formed through said second step are semiconductor layers having the same conductivity type, and the deposited film formed through said second step is at a position on the beltlike substrate different from a position of the deposited film formed through said first step .

4. (Currently Amended) A deposited-film formation process in which a source gas is fed into a discharge space of a reactor, a plurality of discharge means are disposed in the reactor and an electric power is applied to generate discharge in the discharge space to decompose the source gas, thereby forming a deposited film on a

beltlike substrate; the process comprising transporting the beltlike substrate through the reactor during the film formation and having:

a first step of applying to a first discharge means in a first reactor an electric power larger than that for a second discharge means in a second reactor to generate discharge to form the deposited film; and

a second step of applying to the second discharge means in the second reactor an electric power larger than that for the first discharge means in the first reactor to generate discharge to form the deposited film, said first and second discharge means each being electrodes connected to an RF power source;

said first step and said second step being switched from one to another when film formation temperature is above a preset temperature wherein the deposited film formed through said first step and the deposited film formed through said second step are semiconductor layers having the same conductivity type, and the deposited film formed through said second step is at a position on the beltlike substrate different from a position of the deposited film formed through said first step .

5. (Original) The deposited-film formation process according to claim 2, wherein in the first step the electric power is applied to the second discharge means to generate discharge to an extent that does not affect the film formation, and in the second step the electric power is applied to the first discharge means to generate discharge to an extent that does not affect the film formation.

6. (Original) The deposited-film formation process according to claim 1, wherein the first step and the second step are switched from one to another on the basis of a film formation temperature that has reached a temperature within a temperature range set beforehand.

7. (Original) The deposited-film formation process according to claim 1, wherein said first step and said second step are switched from one to another on the basis of a self-bias voltage that has reached a voltage within a voltage range set beforehand.

8. (Original) The deposited-film formation process according to claim 1, wherein said first step and said second step are switched from one to another on the basis of a self-bias electric current that has reached an electric current within an electric-current range set beforehand.

9. (Original) The deposited-film formation process according to claim 1, wherein said first step and said second step are switched from one to another within a film formation time range set beforehand.

10. (Original) The deposited-film formation process according to claim 1, wherein said first and second discharge means are controlled within a stated temperature range.

11. (Original) The deposited-film formation process according to claim 1, which comprises a step of keeping the electric power applied to said first discharge means and said second discharge means to generate discharge through the respective discharge means when said first step and said second step are switched from one to another.

12. (Original) The deposited-film formation process according to claim 1, wherein, when said first step and said second step are switched from one to another, the electric power for said first discharge means is gradually decreased or increased and the electric power for said second discharge means is gradually increased or decreased.

13. (Cancelled)

14. (Original) The deposited-film formation process according to claim 1, wherein a distance between said first and second discharge means and a substrate on which the deposited films are formed is in the range of from 5 mm to 50 mm, and a pressure at which the deposited films are formed is in the range of from 10 Pa to 800 Pa.

15-25. (Cancelled) .